

## WEST Search History





DATE: Wednesday, April 26, 2006

Hide?	Set Name	Query	Hit Count
		<i>DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ</i>	
<input type="checkbox"/>	L12	L11 with nm	10
<input type="checkbox"/>	L11	plasma radiation	988
<input type="checkbox"/>	L10	L8 with laser with nm	112
<input type="checkbox"/>	L9	L8 and laser and nm	1514
<input type="checkbox"/>	L8	plasma with uv	5971
<input type="checkbox"/>	L7	L6 and (low with k)	101
<input type="checkbox"/>	L6	plasma same (150 with nm)	2845
		<i>DB=USPT; PLUR=YES; OP=ADJ</i>	
<input type="checkbox"/>	L5	'5004964'.pn.	1
<input type="checkbox"/>	L4	'5004964'.pn.	1
		<i>DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ</i>	
<input type="checkbox"/>	L3	ultrasonic same wash\$4 and kataoka	38
<input type="checkbox"/>	L2	ultrasonic same wash\$4 same kataoka	0
<input type="checkbox"/>	L1	ultrasonic and wash\$4 and kataoka	356

END OF SEARCH HISTORY

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L12: Entry 9 of 10

File: DWPI

Dec 2, 1997

DERWENT-ACC-NO: 1998-031954

DERWENT-WEEK: 199803

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TITLE: In situ monitoring of layer etch rate - comprises use of plasma etch system to determine ratio of intensities at two wavelengths

Basic Abstract Text (1):

An in situ method of monitoring the etch rate of a layer comprises providing a silicon substrate (1) bearing a layer and a plasma which emits radiation and etches the layer (4). Power is provided and the substrate placed in the plasma, radiation intensities at 388.5 and 443.7 nm are measured and the quotient of these, which is proportional to the etch rate, computed.

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